

| Ref # | Hits | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|--|---|------------------|---------|------------------|
| S1    | 1099 | epitaxial\$3 near3 (gallium near nitride GaN)                      | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 10:10 |
| S2    | 239  | S1 with buffer   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 09:38 |
| S3    | 5    | thermal\$3 near4 silicon near nitride near3 passivation near layer | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 13:10 |
| S4    | 0    | S2 and S3  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 09:33 |
| S5    | 0    | S1 and S3  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 09:33 |
| S6    | 1    | S2 and thermal\$2 near3 assist\$3                                  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 09:43 |
| S7    | 18   | thermal\$2 near3 assist\$3 with silicon adj nitride                | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 10:07 |
| S8    | 0    | S1 and S7  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 09:43 |
| S9    | 34   | thermal\$2 near3 assist\$3 same silicon adj nitride                | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/01/20 10:07 |

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| S10 | 34   | S9 not S8   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:07 |
| S11 | 16   | S9 not S7   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:07 |
| S12 | 22   | S1 near3 buffer adj layer   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:18 |
| S13 | 0    | S12 and (PSN ((pyrolitic near silicon adj nitride) ((thermally near assisted) near silicon adj nitride)))                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:22 |
| S14 | 1750 | (PSN ((pyrolitic near silicon adj nitride) ((thermally near assisted) near silicon adj nitride)))                             | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:24 |
| S15 | 0    | S12 and S14   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:22 |
| S16 | 0    | S1 and S14  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:22 |
| S17 | 0    | (PSN ((pyrolitic near silicon adj nitride) ((thermally near assisted) near silicon adj nitride))) near5 passivation adj layer | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:23 |
| S18 | 0    | psn near5 passivation adj layer   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 10:24 |
| S19 | 8672 | (438/197,211,257,585,587,594,634,637,672,675,251,261,597). CCLS.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/01/20 10:30 |

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| S20 | 2   | S1 and S19  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/01/20 10:30 |
| S21 | 58  | ((epitaxial\$3 epi 'gna' epitaxy)<br>near3 (layer film)) near5 (silicon<br>adj nitride)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:14 |
| S22 | 22  | S21 and(nitride with (protect\$5<br>passivat\$5))   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:15 |
| S23 | 677 | ((epitaxial\$3 epi 'gna' epitaxy)<br>near3 (layer film)) near5 (silicon<br>adj nitride)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 14:02 |
| S24 | 164 | S23 and(nitride with (protect\$5<br>passivat\$5))   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 14:08 |
| S25 | 75  | S24 and (nitride with (heat\$4<br>thermal\$4 dens\$4))                                    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:16 |
| S26 | 958 | ((buffer 'gan' gallium adj nitride)<br>near5 (layer film)) near5 (silicon<br>adj nitride) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:19 |
| S27 | 53  | S26 and ((buffer 'gan' gallium adj<br>nitride) near5 (epitaxial epi 'gna'<br>epitaxy))    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:28 |
| S28 | 9   | S27 and schottky  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:30 |
| S29 | 0   | S27 and 'AlGaN' near schottky   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 13:30 |

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| S30 | 18   | structur\$4 near5 (((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film)) near5 (silicon adj nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 13:50 |
| S31 | 1    | S30 and ('AlGaIn' aluminum near gallium near nitride)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 13:52 |
| S32 | 1    | S21 and ('AlGaIn' aluminum near gallium near nitride)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 13:53 |
| S33 | 5    | S23 and ('AlGaIn' aluminum near gallium near nitride)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:03 |
| S34 | 217  | hemt and misfet   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:02 |
| S35 | 0    | S23 and S34   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:01 |
| S36 | 80   | S34 and ((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film))   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:39 |
| S37 | 23   | S36 and ('AlGaIn' aluminum near gallium near nitride)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:11 |
| S38 | 3    | "I23" and (nitride with (protect\$5 passivat\$5))   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:40 |
| S39 | 5171 | 'led' and ((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film))                                       | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/01/20 14:10 |

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| S40 | 5171  | S39 and ((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film)) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:11 |
| S41 | 934   | S40 and ('AlGaIn' aluminum near gallium near nitride)         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:42 |
| S42 | 16    | S26 and S41   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:12 |
| S43 | 73105 | ((epitaxial\$3 epi 'gna' epitaxy) near3 (layer film))         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:39 |
| S44 | 3     | S38 and (nitride with (protect\$5 passivat\$5))               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:40 |
| S45 | 0     | S37 and (nitride with (protect\$5 passivat\$5))               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:41 |
| S46 | 3     | S44 and (nitride with (protect\$5 passivat\$5))               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:41 |
| S47 | 3360  | S43 and (nitride with (protect\$5 passivat\$5))               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:45 |
| S48 | 140   | S47 and ('AlGaIn' aluminum near gallium near nitride)         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:46 |
| S49 | 1998  | S43 and (silicon near nitride with (protect\$5 passivat\$5))  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/01/20 14:45 |

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| S50 | 59 | S49 and ('AlGaN' aluminum near gallium near nitride)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 16:00 |
| S51 | 12 | (("6384433") or ("6387733") or ("6448973") or ("6560452") or ("6633073") or ("6750482")).PN. | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/01/20 15:53 |
| S52 | 51 | pyrolosis  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 16:01 |
| S53 | 3  | pyrolosis and silicon adj nitride  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 16:07 |
| S54 | 2  | pyrolosis with silicon adj nitride   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/01/20 16:07 |